



03345-P0013A WWW/TMO

PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants	Bernd Schoettker, <i>et al.</i>
Serial No. 09/624,252	Filing Date: July 24, 2000
Title of Application	Method For Growing Nitrogenous Semiconductor Crystal Materials

Box DAC  
Assistant Commissioner for Patents  
Washington, DC 20231

1742/9  
#9  
RECEIVED  
FEB 05 2002  
TC 1700

**PETITION FOR CORRECTION OF INVENTORSHIP IN A PATENT  
APPLICATION OTHER THAN A REISSUE APPLICATION (37 C.F.R. 1.48(a))**

Dear Sir:

Applicant, through its undersigned attorneys, hereby petitions under 37 CFR 1.48(a) that the inventorship of the above-identified application be corrected as reflected on the Declaration and Power of Attorney attached hereto. The application as originally filed mistakenly listed only the first named inventor, and accidentally omitted the four other inventors.

Mailing Certificate: I hereby certify that this correspondence is today being deposited with the U.S. Postal Service as *First Class Mail* in an envelope addressed to: Box DAC; Assistant Commissioner for Patents; Washington, DC 20231.

December 11, 2001

*Beatrice R. Emerson*  
Beatrice R. Emerson

1. **Statement of Lack of Deceptive Intent.** The application as originally filed mistakenly listed only the first named inventor, and accidentally omitted the four other inventors. This error in inventorship occurred without deceptive intention on the part of the persons who through error were not named as inventors. Attached hereto as Exhibit A is a Statement of Lack of Deceptive Intention, executed by the persons who through error were not named as inventors, as required by 37 C.F.R. 1.48(a)(1).
2. **Declaration and Power of Attorney.** Attached hereto as Exhibit B is a Declaration and Power of Attorney in compliance with 37 C.F.R. 1.63 which has been executed by all five of the actual inventors, as required by 37 C.F.R. 1.48(a)(2).
3. **Petition Fee.** Enclosed herewith is a check for \$130.00 in accordance with 37 CFR 1.17(i), as required by 37 C.F.R. 1.48(a)(3). The undersigned hereby requests that any additional fee which is due be charged to Account Number 19-4516
4. **Consent of Assignee.** An assignment has been executed by the original named inventor. Therefore, Attached hereto as Exhibit C is a Consent of Assignee in compliance with 37 C.F.R. 3.73(b), as required by 37 C.F.R. 1.48(a)(4).

Respectfully submitted,



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Wesley W. Whitmyer, Jr., Registration No. 33,558  
Todd M. Oberdick, Registration No. 44,268  
Attorneys for Applicant  
ST.ONGE STEWARD JOHNSTON & REENS LLC  
986 Bedford Street  
Stamford, CT 06905-5619  
203 324-6155



Ai 2000/07

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Applicants	Bernd Schoettker, et al.
Serial No. 09/624,252	Filing Date: July 24, 2000
Title of Application	Method For Growing Nitrogenous Semiconductor Crystal Materials

**STATEMENT OF LACK OF DECEPTIVE INTENTION  
IN SUPPORT OF PETITION UNDER 37 C.F.R. 1.48(a)**RECEIVED  
FEB 05 2002  
TC 1700

Dear Sir:

In support of the Petition For Correction of Inventorship (37 CFR 1.48(a)) in connection with which this Statement is being filed, we, the undersigned, state that the application as originally filed mistakenly listed only the first named inventor, and accidentally omitted we four other inventors. We further state that this the aforementioned error in inventorship occurred without any deceptive intention.

We hereby declare that all statements made herein of our own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title

## Statement Of Lack of Deceptive Intention

Serial No. 09/624,252

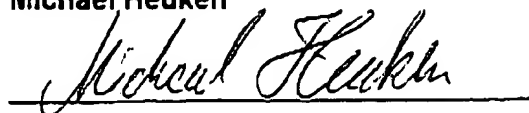
Applicants: Bernd Schoettker, et al.

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18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

**Michael Heuken**

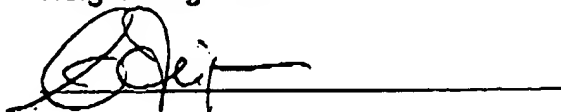
Inventor's signature



Date:

15.11.01**Holger Jürgensen**

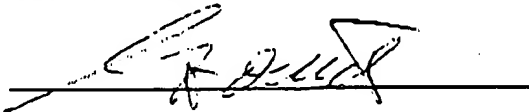
Inventor's signature



Date:

12/3/01**Gerd Strauch**

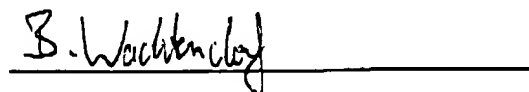
Inventor's signature



Date:

14/11/01**Bernd Wachtendorf**

Inventor's signature



Date:

21.11.01

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**Declaration and Power of Attorney**

As below-named inventors, we hereby declare that:

Our residences, post office addresses, and citizenships are as stated below next to our names.

We believe that we are the original, first and joint inventors of the subject matter which is claimed and for which a patent is sought on the invention entitled **Method For Growing Nitrogenous Semiconductor Crystal Materials**, bearing Serial No. 09/624,252, filed July 24, 2000.

We hereby state that we have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above. To the best of our knowledge, information, and belief the facts stated therein are true.

We acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, §1.56.

We hereby claim foreign priority benefits under Title 35, United States Code, §119 of any foreign applications for patent or inventor's certificate listed below and have also identified below any foreign applications for patent or inventor's certificate having a filing date before that of the application on which priority is claimed.

German Application No. DE 100 18 128.7 filed April 12, 2000

We hereby claim the benefit under Title 35, United States Code, §120 of the following United States Applications listed below, and insofar as the subject matter of each of the claims of this Application is not disclosed in the prior United States Application in the manner provided by the first paragraph of Title 35, United States Code, §112, we acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, §1.56 which occurred between the filing date of the prior application and the national or PCT international filing date of this application.

None

We hereby declare that all statements made herein of our own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false

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Declaration and Power of Attorney  
Serial No. 09/624,252

statements may jeopardize the validity of the application or any patent issued thereon.

We hereby appoint Wesley W. Whitmyer, Jr., Registration No. 33,558, of ST. ONGE STEWARD JOHNSTON & REENS LLC; 986 Bedford Street; Stamford, Connecticut 06905-5619 (203 324-6155); with full power of substitution, association and revocation, as attorney to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all telephone calls and correspondence to Wesley W. Whitmyer, Jr. at the above address and telephone number.

Full name of first inventor:

Bernd Schnettker

Inventor's signature



Date:

19. Nov. 01

Residence:

D-52072 Aachen, Germany

Citizenship:

A citizen of Germany

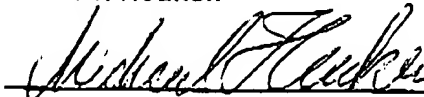
Post Office Address:

Nizzaallee 44  
D-52072 Aachen  
Germany

Full name of second inventor:

Michael Heuken

Inventor's signature



Date:

15. 11. 01

Residence:

D-52078 Aachen, Germany

Citizenship:

A citizen of Germany

Post Office Address:

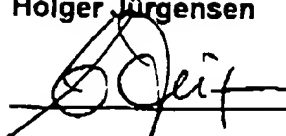
Im Erb 12  
D-52078 Aachen  
Germany

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Declaration and Power of Attorney  
Serial No. 09/624,252

Full name of Third inventor:

Holger Jürgensen

Inventor's signature



Date:

21.11.01

Residence:

D-52072 Aachen, Germany

Citizenship:

A citizen of Germany

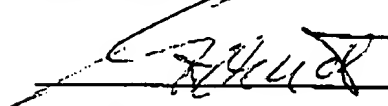
Post Office Address:

Rathausstrasse 43d  
D-52072 Aachen  
Germany

Full name of Fourth inventor:

Gerd Strauch

Inventor's signature



Date:

14/11/01

Residence:

D-52072 Aachen, Germany

Citizenship:

A citizen of Germany

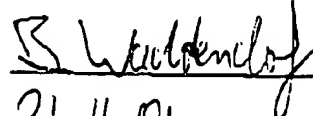
Post Office Address:

Schönauer Friede 80  
D-52072 Aachen  
Germany

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Declaration and Power of Attorney  
Serial No. 09/624,252Full name of Fifth inventor:**Bernd Wachtendorf**

Inventor's signature



Date:

21.11.01

Residence:

Hsin-Chu, 300, Taiwan, R.O.C.

Citizenship:

A citizen of China

Post Office Address:

Rm. # 19, 8F  
No. 8. Chu-Kuang Road  
Hsin-Chu, 300  
Taiwan, R.O.C.



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WRITTEN CONSENT OF ASSIGNEE OF RECORD (37 CFR 3.73(b))  
IN SUPPORT OF PETITION UNDER 37 C.F.R. 1.48(a)

The assignee of record, AIXTRON AG, hereby gives consent to the inventorship correction requested through the Petition For Correction of Inventorship (37 CFR 1.48(a)) in connection with which this Written Consent is being filed. AIXTRON AG is sole owner of the aforesaid patent application for which correction of inventorship is sought by virtue of an assignment recorded with the U.S. Patent and Trademark Office on Reel 011526 Frame 0695. The individual signing below hereby states that he or she has authority to act on behalf of the assignee, AIXTRON AG.

Dated: 11-19-01

By: 

Name: Dr. Holger Jürgensen

Title: BOARD